

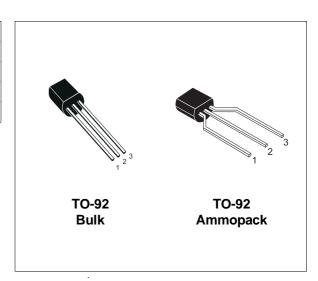
SMALL SIGNAL NPN TRANSISTORS

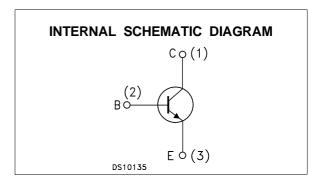
Ordering Code	Marking	Package / Shipment		
BC547B	BC547B	TO-92 / Bulk		
BC547B-AP	BC547B	TO-92 / Ammopack		
BC547C	BC547C	TO-92 / Bulk		
BC547C-AP	BC547C	TO-92 / Ammopack		

- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- TO-92 PACKAGE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY
- BC547B THE PNP COMPLEMENTARY TYPE IS BC557B

APPLICATIONS

- WELL SUITABLE FOR TV AND HOME APPLIANCE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTORS WITH HIGH GAIN AND LOW SATURATION VOLTAGE





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I _E = 0)	50	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	45	V
V _E BO	Emitter-Base Voltage (Ic = 0)	6	V
Ic	Collector Current	100	mA
I _{CM}	Collector Peak Current (t _p < 5 ms)	200	mA
P_{tot}	Total Dissipation at T _C = 25 °C	500	mW
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

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THERMAL DATA

F	R _{thj-amb} •	Thermal	Resistance	Junction-Ambient	Max	250	°C/W	
F	R _{thj-Case} •	Thermal	Resistance	Junction-Case	Max	83.3	°C/W	

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

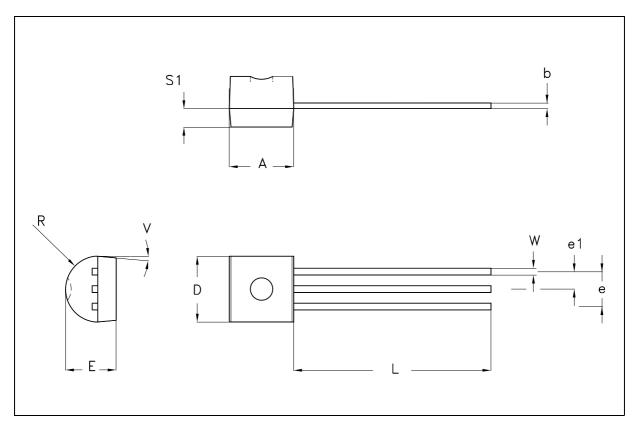
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	$V_{CB} = 30 \text{ V}$ $V_{CB} = 30 \text{ V}$ $T_{C} = 150 ^{\circ}\text{C}$			15 5	nΑ μΑ
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			100	nA
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	Ic = 10 mA	45			V
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	I_C = 10 mA I_B = 0.5 mA I_C = 100 mA I_B = 5 mA		0.09 0.2	0.25 0.6	V
$V_{BE(sat)^*}$	Base-Emitter Saturation Voltage	$I_{C} = 10 \text{ mA}$ $I_{B} = 0.5 \text{ mA}$ $I_{C} = 100 \text{ mA}$ $I_{B} = 5 \text{ mA}$		0.7 0.9		V
V _{BE(on)} *	Base-Emitter On Voltage	I _C = 2 mA	0.58	0.66	0.7 0.77	V
h _{FE}	DC Current Gain	I _C = 2 mA	200 420		450 800	
f _T	Transition Frequency	$I_C = 10 \text{ mA } V_{CE} = 5 \text{ V } f = 100 \text{MHz}$	100			MHz
Ссво	Collector-Base Capacitance	IE = 0 VCB = 10 V f = 1 MHz		1.5		pF
C _{EBO}	Emitter-Base Capacitance	$I_C = 0$ $V_{EB} = 0.5 \text{ V}$ $f = 1 \text{ MHz}$		11		pF
NF	Noise Figure	$V_{CE} = 5 \text{ V}$ $I_C = 200 \mu\text{A}$ $f = 1 \text{KHz}$ $\Delta f = 200 \text{Hz}$ $R_G = 2 \text{K}\Omega$		2	10	dB

^{*} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 2 %

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TO-92 MECHANICAL DATA

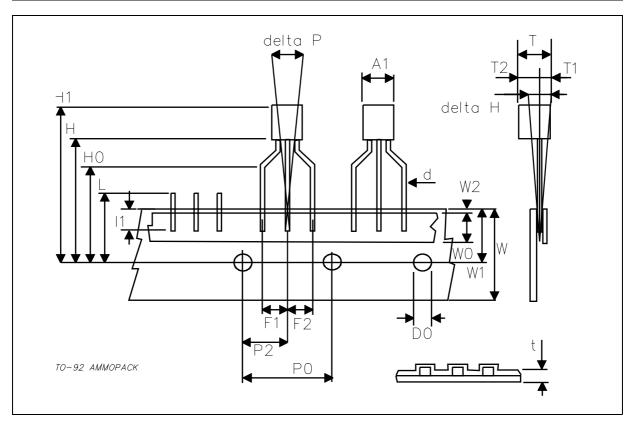
DIM.	mm			inch		
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.32		4.95	0.170		0.195
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
Е	3.30		3.94	0.130		0.155
е	2.41		2.67	0.095		0.105
e1	1.14		1.40	0.045		0.055
L	12.70		15.49	0.500		0.609
R	2.16		2.41	0.085		0.094
S1	1.14		1.52	0.045		0.059
W	0.41		0.56	0.016		0.022
V	4 degree		6 degree	4 degree		6 degree



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TO-92 AMMOPACK SHIPMENT (Suffix"-AP") MECHANICAL DATA

DIM.		mm		inch		
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A1			4.80			0.189
Т			3.80			0.150
T1			1.60			0.063
T2			2.30			0.091
d			0.48			0.019
P0	12.50	12.70	12.90	0.492	0.500	0.508
P2	5.65	6.35	7.05	0.222	0.250	0.278
F1,F2	2.44	2.54	2.94	0.096	0.100	0.116
delta H	-2.00		2.00	-0.079		0.079
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.70	6.00	6.30	0.224	0.236	0.248
W1	8.50	9.00	9.25	0.335	0.354	0.364
W2			0.50			0.020
Н	18.50		20.50	0.728		0.807
H0	15.50	16.00	16.50	0.610	0.630	0.650
H1			25.00			0.984
D0	3.80	4.00	4.20	0.150	0.157	0.165
t			0.90			0.035
L			11.00			0.433
I1	3.00			0.118		
delta P	-1.00		1.00	-0.039		0.039



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